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# Memory Stick™ INTERCONNECT EXTENDER CHIPSET WITH LVDS SN65LVDT14 – ONE DRIVER PLUS FOUR RECEIVERS SN65LVDT41 – FOUR DRIVERS PLUS ONE RECEIVER

#### **FEATURES**

- Controlled Baseline
  - One Assembly/Test Site, One Fabrication Site
- Enhanced Diminishing Manufacturing Sources (DMS) Support
- Enhanced Product-Change Notification
- Qualification Pedigree (1)
- Integrated 110- $\Omega$  Nominal Receiver Line Termination Resistor
- Operate From a Single 3.3-V Supply
- Greater Than 125-Mbps Data Rate
- Flow-Through Pinout
- LVTTL-Compatible Logic I/Os
- ESD Protection on Bus Pins Exceeds 12 kV
- Meet or Exceed Requirements of ANSI/TIA/EIA-644A Standard for LVDS
- 20-Pin Thin Shrink Small-Outline Package (PW) With 26-Mil Terminal Pitch
- (1) Component qualification in accordance with JEDEC and industry standards to ensure reliable operation over an extended temperature range. This includes, but is not limited to, Highly Accelerated Stress Test (HAST) or biased 85/85, temperature cycle, autoclave or unbiased HAST, electromigration, bond intermetallic life, and mold compound life. Such qualification testing should not be viewed as justifying use of this component beyond specified performance and environmental limits.

#### **APPLICATIONS**

- Memory Stick<sup>™</sup> Interface Extensions With Long Interconnects Between Host and Memory Stick
- Serial Peripheral Interface<sup>™</sup> (SPI<sup>™</sup>) Interface Extension to Allow Long Interconnects Between Master and Slave
- MultiMediaCard™ (MMC) Interface in SPI Mode
- General-Purpose Asymmetric Bidirectional Communication

#### DESCRIPTION

The SN65LVDT14 combines one LVDS line driver with four terminated LVDS line receivers in one package. It is designed to be used at the Memory Stick $^{\text{TM}}$  end of an LVDS-based Memory Stick interface extension.

The SN65LVDT41 combines four LVDS line drivers with a single terminated LVDS line receiver in one package. It is designed to be used at the host end of an LVDS-based Memory Stick interface extension.

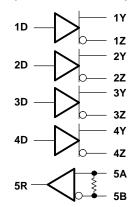


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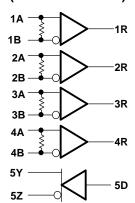
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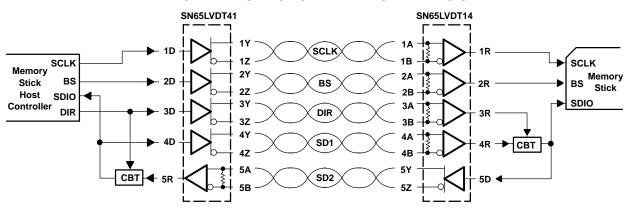
# SN65LVDT41 LOGIC DIAGRAM (POSITIVE LOGIC)



# SN65LVDT14 LOGIC DIAGRAM (POSITIVE LOGIC)



#### TYPICAL MEMORY STICK INTERFACE EXTENSION



# **Absolute Maximum Ratings**(1)

over operating free-air temperature range (unless otherwise noted)

				SN65LVI SN65LVI	,	UNIT
				MIN	MAX	
$V_{CC}$	Supply voltage range (2)			-0.5	4	V
	lanut voltage range	D or R	D or R		6	V
	Input voltage range	A, B, Y, or Z		-0.5	4	V
		Liverage Dady Madal(3)	A, B, Y, Z, and GND		±12	KV
	Electrostatic discharge	Human-Body Model (3)	All pins		±8	ΚV
		Charged-Device Model (4)	All pins		±500	V
	Continuous total power dissipation					ing Table
	Storage temperature range			-65	150	°C
	Lead temperature 1,6 mm	(1/16 in) from case for 10 s			260	°C

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.
- (3) Tested in accordance with JEDEC Standard 22, Test Method A114-A
- (4) Tested in accordance with JEDEC Standard 22, Test Method C101



# **Package Dissipation Ratings**

PACKAGE	T <sub>A</sub> < 25°C	OPERATING FACTOR	T <sub>A</sub> = 85°C	T <sub>A</sub> = 125°C
	POWER RATING	ABOVE T <sub>A</sub> = 25°C	POWER RATING	POWER RATING
PW	774 mW	6.2 mW/°C	402 mW	154 mW

# **Recommended Operating Conditions**

		MIN	NOM	MAX	UNIT
$V_{CC}$	Supply voltage range	3	3.3	3.6	V
V <sub>IH</sub>	High-level input voltage	2			V
V <sub>IL</sub>	Low-level input voltage			0.8	V
V <sub>ID</sub>	Magnitude of differential input voltage	0.1		0.6	V
V <sub>IC</sub>	Common-mode input voltage (see Figure 1)	$\frac{ V_{ID} }{2}$		$2.4-\frac{ V_{ID} }{2}$	V
				$V_{CC} - 0.8$	
T <sub>A</sub>	Operating free-air temperature	-40		125	°C

# COMMON-MODE INPUT VOLTAGE vs

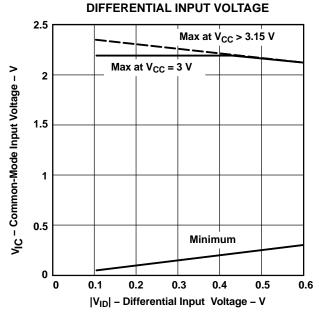


Figure 1.  $V_{\text{IC}}$  vs  $V_{\text{ID}}$  and  $V_{\text{CC}}$ 



#### **Receiver Electrical Characteristics**

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
$V_{\text{ITH+}}$	Positive-going differential input voltage threshold	See Figure 2 and Table 1			100	mV
V <sub>ITH</sub> _	Negative-going differential input voltage threshold	See Figure 2 and Table 1	-100			mV
V <sub>OH</sub>	High-level output voltage	I <sub>OH</sub> = -8 mA	2.4			V
$V_{OL}$	Low-level output voltage	I <sub>OL</sub> = 8 mA			0.4	V
I <sub>I</sub>	Input current (A or B inputs)	$V_I = 0 \text{ V}$ and $V_I = 2.4 \text{ V}$ , Other input open			±40	μΑ
$I_{I(OFF)}$	Power-off input current (A or B inputs)	$V_{CC} = 0 \text{ V}, V_{I} = 2.4 \text{ V}$			±40	μΑ
C <sub>i</sub>	Input capacitance, A or B input to GND	$V_I = A \sin 2\pi ft + CV$		5		pF
Z <sub>t</sub>	Termination impedance	V <sub>ID</sub> = 0.4 sin2.5E09 t V	88		132	Ω

<sup>(1)</sup> All typical values are at 25°C and with a 3.3-V supply.

# **Driver Electrical Characteristics**

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
V <sub>OD</sub>	Differential output voltage magnitude	$R_L = 100 \Omega$ , See Figure 3 and Figure 5	247	340	454	mV
$\Delta  V_{OD} $	Change in differential output voltage magnitude between logic states	$R_L = 100 \Omega$ , See Figure 3 and Figure 5	-50		50	mV
V <sub>OC(SS)</sub>	Steady-state common-mode output voltage	See Figure 6	1.125		1.375	V
$\Delta V_{OC(SS)}$	Change in steady-state common-mode output voltage between logic states	See Figure 6	-50		50	mV
V <sub>OC(PP)</sub>	Peak-to-peak common-mode output voltage	See Figure 6		50		mV
I <sub>IH</sub>	High-level input current	V <sub>IH</sub> = 2 V			20	μΑ
I <sub>IL</sub>	Low-level input current	V <sub>IL</sub> = 0.8 V			10	μΑ
	Chart sire it autout aurent	V <sub>OY</sub> or V <sub>OZ</sub> = 0 V			±24	A
Ios	Short-circuit output current	$V_{OD} = 0 \ V^{(2)}$			±12	mA
I <sub>O(OFF)</sub>	Power-off output current	$V_{CC} = 1.5 \text{ V}, V_{O} = 2.4 \text{ V}$			±1	μΑ

# **Device Electrical Characteristics**

over operating free-air temperature range (unless otherwise noted)

	PARAMETE	R	TEST CONDITIONS	MIN	MAX	UNIT
	Cupply ourront	SN65LVDT14	Driver $R_L = 100 \Omega$ , Driver $V_I = 0.8 V$ or 2 V,		25	mΛ
ICC	Supply current	SN65LVDT41	Receiver $V_1 = \pm 0.4 \text{ V}$		35	mA

<sup>(1)</sup> All typical values are at 25°C and with a 3.3-V supply.(2) This parameter is GBD over industrial temperature range.

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# **Receiver Switching Characteristics**

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	NOM	MAX	UNIT
t <sub>PLH</sub>	Propagation delay time, low- to high-level output		1	2.6	4.8	ns
t <sub>PHL</sub>	Propagation delay time, high- to low-level output		1	2.6	4.8	ns
t <sub>r</sub>	Output signal rise time		0.15		1.4	ns
t <sub>f</sub>	Output signal fall time	C <sub>L</sub> = 10 pF, See Figure 4	0.15		1.4	ns
t <sub>sk(p)</sub>	Pulse skew ( t <sub>PHL</sub> - t <sub>PLH</sub>  )			150	750	ps
t <sub>sk(o)</sub>	Output skew <sup>(1)</sup>			100	550	ps
t <sub>sk(pp)</sub>	Part-to-part skew <sup>(2)</sup>				1	ns

t<sub>sk(0)</sub> is the magnitude of the time difference between the t<sub>PLH</sub> or t<sub>PHL</sub> of all the receivers of a single device with all of their inputs connected together.

# **Driver Switching Characteristics**

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	NOM	MAX	UNIT
t <sub>PLH</sub>	Propagation delay time, low- to high-level output		0.9	1.7	3.9	ns
t <sub>PHL</sub>	Propagation delay time, high- to low-level output		0.9	1.6	3.9	ns
t <sub>r</sub>	Differential output signal rise time		0.26		1.2	ns
t <sub>f</sub>	Differential output signal fall time	$R_L = 100 \Omega$ , $C_L = 10 pF$ , See Figure 7	0.26		1.2	ns
t <sub>sk(p)</sub>	Pulse skew ( t <sub>PHL</sub> - t <sub>PLH</sub>  )	_ Gee riguie r		150	750	ps
t <sub>sk(o)</sub>	Output skew <sup>(1)</sup>			80	400	ps
t <sub>sk(pp)</sub>	Part-to-part skew <sup>(2)</sup>				1.5	ns

 $t_{sk(pp)}$  is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

 <sup>(1)</sup> t<sub>sk(p)</sub> is the magnitude of the time difference between the high-to-low and low-to-high propagation delay times at an output.
 (2) t<sub>sk(pp)</sub> is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.



# PARAMETER MEASUREMENT INFORMATION

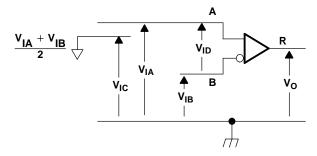
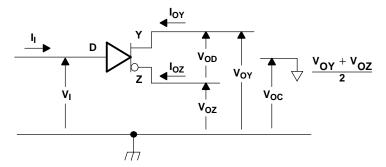


Figure 2. Receiver Voltage Definitions

Table 1. Receiver Minimum and Maximum Input Threshold Test Voltages

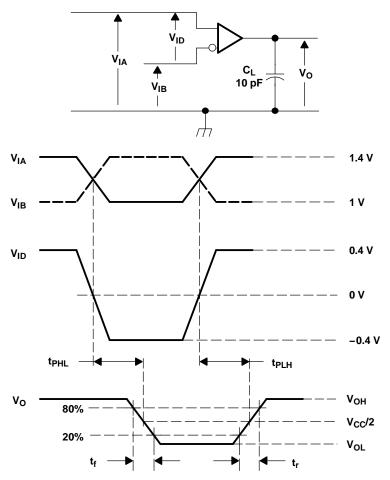
APPLIED	) VOLTAGE	RESULTING DIFFERENTIAL INPUT VOLTAGE	RESULTING COMMON-MODE INPUT VOLTAGE
V <sub>IA</sub>	V <sub>IB</sub>	V <sub>ID</sub>	V <sub>IC</sub>
1.25 V	1.15 V	100 mV	1.2 V
1.15 V	1.25 V	−100 mV	1.2 V
2.4 V	2.3 V	100 mV	2.35 V
2.3 V	2.4 V	−100 mV	2.35 V
0.1 V	0 V	100 mV	0.05 V
0 V	0.1 V	−100 mV	0.05 V
1.5 V	0.9 V	600 mV	1.2 V
0.9 V	1.5 V	−600 mV	1.2 V
2.4 V	1.8 V	600 mV	2.1 V
1.8 V	2.4 V	−600 mV	2.1 V
0.6 V	0 V	600 mV	0.3 V
0 V	0.6 V	−600 mV	0.3 V



**Figure 3. Driver Voltage and Current Definitions** 



# PARAMETER MEASUREMENT INFORMATION



A. All input pulses are supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 1$  ns, pulse repetition rate (PRR) = 1 Mpps, pulse width = 0.5  $\pm$  0.05  $\mu$ s.  $C_L$  includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T.

Figure 4. Receiver Timing Test Circuit and Waveforms



#### PARAMETER MEASUREMENT INFORMATION

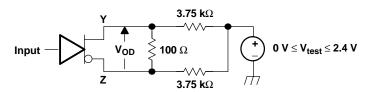
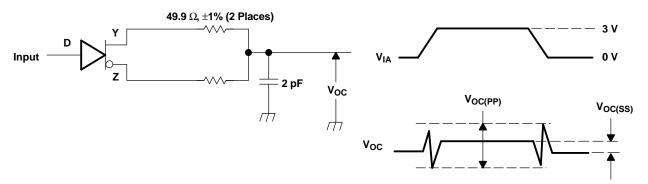
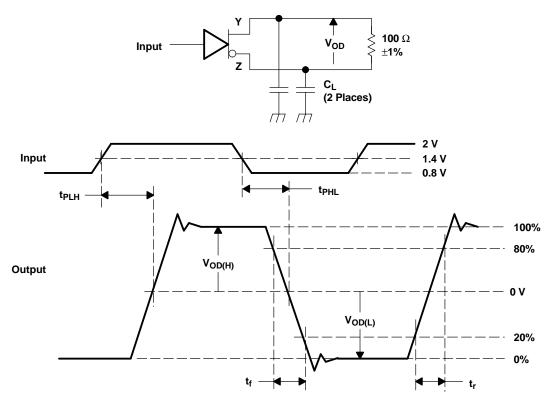


Figure 5. Driver VDO Test Circuit



A. All input pulses are supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 1$  ns, pulse repetition rate (PRR) = 0.5 Mpps, pulse width =  $500 \pm 10$   $\mu$ s.  $C_L$  includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T. The measurement of  $V_{OC(PP)}$  is made on test equipment with a -3-dB bandwidth of at least 1 GHz.

Figure 6. Test Circuit and Definitions for Driver Common-Mode Output Voltage



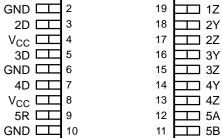
A. All input pulses are supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 1$  ns, pulse repetition rate (PRR) = 1 Mpps, pulse width = 0.5  $\pm$  0.05  $\mu$ s.  $C_L$  includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T.

Figure 7. Test Circuit, Timing, and Voltage Definitions for Differential Output Signal



### SN65LVDT41 (Marked as LVDT41)

# 1D 10 20 1Y



#### SN65LVDT14 (Marked as LVDT14)

1A	1 O 2 3 4 5 6 7 8	20 19 18 17 16 15 14	1R GND 2R 3R GND 4R Vcc
	8 9 10		

# **FUNCTION TABLES**

# RECEIVER(1)

INPUTS	OUTPUT
$V_{ID} = V_A - V_B$	R
$V_{ID} \ge 100 \text{ mV}$	Н
$-100 \text{ mV} < V_{\text{ID}} < 100 \text{ mV}$	?
$V_{ID} \le -100 \text{ mV}$	L
Open	Н

(1) H = high level, L = low level, ? = indeterminate

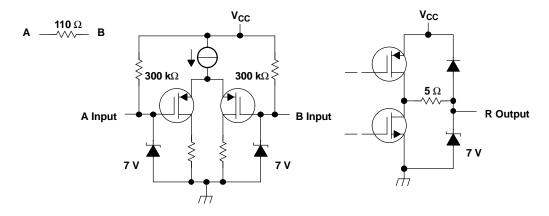
# DRIVER<sup>(1)</sup>

INPUT	OUTPUTS		
D	Y	Z	
Н	Н	L	
L	L	Н	
Open	L	Н	

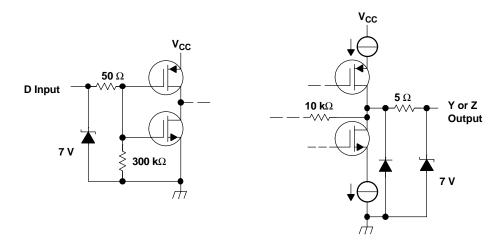
(1) H = high level, L = low level



# RECEIVER EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS



# DRIVER EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS



**LOW-LEVEL OUTPUT VOLTAGE** 

**LOW-LEVEL OUTPUT CURRENT** 



# TYPICAL CHARACTERISTICS Receiver

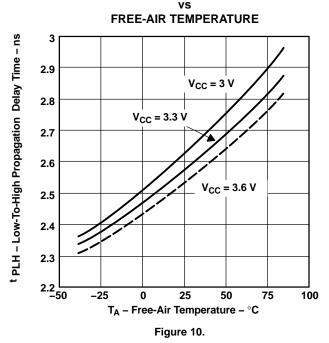
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# **HIGH-LEVEL OUTPUT VOLTAGE HIGH-LEVEL OUTPUT CURRENT** $T_A = 25^{\circ}C$ $V_{CC} = 3.3 \text{ V}$ 3.5 VOH - High-Level Output Voltage - V 3 2.5 1.5 1 0.5 -70 -50 -40 -30 -20 -10 I<sub>OH</sub> – High-Level Output Current – mA

# 

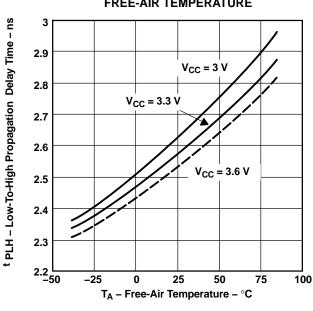
# LOW-TO-HIGH PROPAGATION DELAY TIME

Figure 8.



# LOW-TO-HIGH PROPAGATION DELAY TIME vs FREE-AIR TEMPERATURE

Figure 9.





# TYPICAL CHARACTERISTICS Driver

# LOW-TO-HIGH PROPAGATION DELAY TIME

# FREE-AIR TEMPERATURE 2.1 <sup>t</sup> PLH – Low-To-High Propagation Delay Time – ns $V_{CC} = 3 V$ 1.9 1.8 $V_{CC} = 3.6 \text{ V}$ 1.7 1.6 $V_{CC} = 3.3 V$ 1.5 -50 -25 50 75 100 $T_A$ – Free-Air Temperature – $^{\circ}C$

# Figure 12.

# HIGH-TO-LOW PROPAGATION DELAY TIME

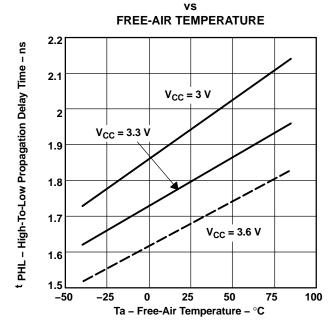


Figure 13.



#### **APPLICATION INFORMATION**

#### Extending the Memory Stick Interface Using LVDS Signaling Over Differential Transmission Cables

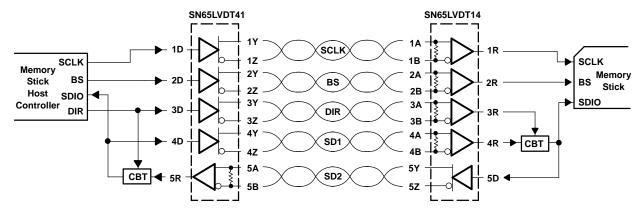


Figure 14. System-Level Block Diagram

The Memory Stick signaling interface operates in a master-slave architecture, with three active signal lines. The host (master) supplies a clock (SCLK) and bus-state (BS) signal to control the operation of the system. The SCLK and BS signals are unidirectional (simplex) from the host to the Memory Stick. The serial data input/output (SDIO) signal is a bidirectional (half-duplex) signal used to communicate both control and data information between the host and the Memory Stick. The direction of data control is managed by the host through a combination of BS line states and control information delivered to the Memory Stick.

The basic Memory Stick interface is capable of operating only over short distances due to the single-ended nature of the digital I/O signals. Such a configuration is entirely suitable for compact and portable devices where there is little if any separation between the host and the Memory Stick. In applications where a greater distance is needed between the host controller and the Memory Stick, it is necessary to utilize a different signaling method, such as low-voltage differential signaling, or LVDS.

LVDS, as specified by the TIA/EIA-644-A standard, provides several benefits when compared to alternative long-distance signaling technologies: low radiated emissions, high noise immunity, low power consumption, and inexpensive interconnect cables.

This device pair provides the necessary LVDS drivers and receivers specifically targeted at implementing a Memory Stick interconnect extension. It utilizes simplex links for the SCLK and BS signals and two simplex links for the SDIO data. The half-duplex SDIO data is split into two simplex streams under control of the host processor by means of the direction (DIR) signal. The DIR signal also is carried from the host to the Memory Stick on a simplex LVDS link.

The switching of the SDIO signal-flow direction in the single-ended interfaces is managed by electronic switch devices, identified by the CBT symbol in Figure 7. A suggested CBT device for this application is the TI SN74CBTLV1G125. These devices are available in space-saving SOT-23 or SC-70 packages.

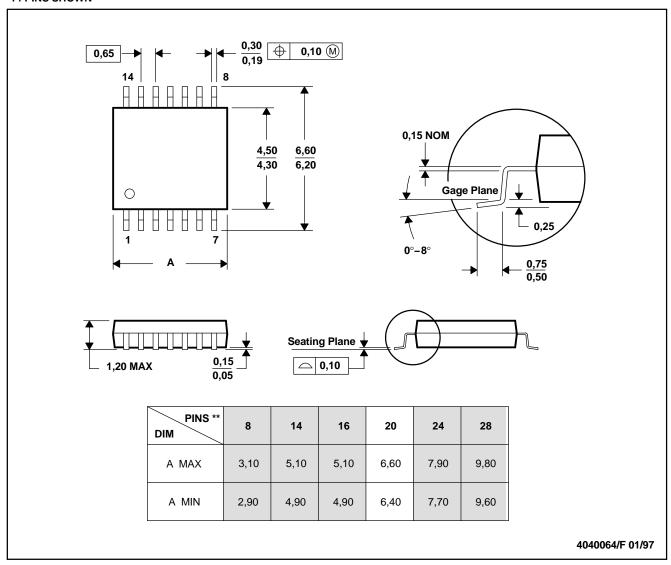


# **MECHANICAL DATA**

# PW (R-PDSO-G\*\*)

#### PLASTIC SMALL-OUTLINE PACKAGE

#### 14 PINS SHOWN

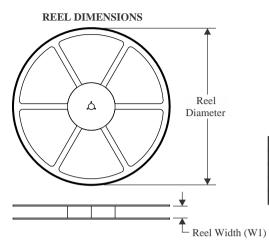


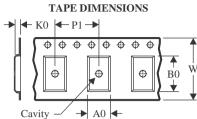
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
- D. Falls within JEDEC MO-153

# **PACKAGE MATERIALS INFORMATION**

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# TAPE AND REEL INFORMATION





	•
A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

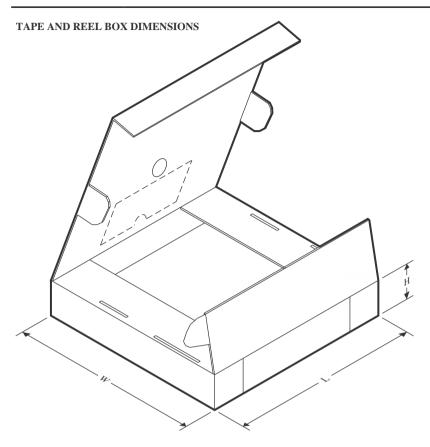


#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65LVDT14QPWREP	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
SN65LVDT41QPWREP	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1

# **PACKAGE MATERIALS INFORMATION**

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# \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LVDT14QPWREP	TSSOP	PW	20	2000	356.0	356.0	35.0
SN65LVDT41QPWREP	TSSOP	PW	20	2000	356.0	356.0	35.0



SMALL OUTLINE PACKAGE



### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



# PW (R-PDSO-G20)

# PLASTIC SMALL OUTLINE



NOTES:

- All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
  C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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